Unit: mm

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type ( $L^2-\pi$ -MOSV)

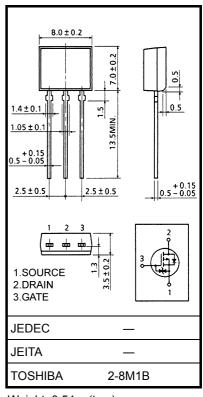
# 2SJ525

Chopper Regulator, DC–DC Converter and Motor Drive Applications

- 4-V gate drive
- Low drain-source ON resistance  $: R_{DS} (ON) = 0.1 \Omega (typ.)$
- High forward transfer admittance  $|Y_{fs}| = 4.5 \text{ S (typ.)}$
- Low leakage current  $: I_{DSS} = -100 \ \mu A \ (max) \ (V_{DS} = -30 \ V)$
- Enhancement mode  $: V_{th} = -0.8 \sim -2.0 \text{ V} (V_{DS} = -10 \text{ V}, \text{ I}_{D} = -1 \text{ mA})$

#### Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	-30	V	
Drain-gate voltage (R <sub>GS</sub> = 20 kΩ)		V <sub>DGR</sub>	-30	V	
Gate-source voltage		V <sub>GSS</sub>	±20	V	
Drain current	DC (Note 1)	I <sub>D</sub>	-5	А	
	Pulse (Note 1)	I <sub>DP</sub>	-20	А	
Drain power dissipation	n (Ta = 25°C)	PD	1.3	W	
Single pulse avalanche energy (Note 2)		E <sub>AS</sub>	517	mJ	
Avalanche current		I <sub>AR</sub>	-5	А	
Repetitive avalanche energy (Note 3)		E <sub>AR</sub>	0.13	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	



Weight: 0.54 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	R <sub>th (ch−a)</sub>	96.1	°C / W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD} = -25 \text{ V}$ ,  $T_{ch} = 25^{\circ}\text{C}$  (initial), L = 14.84 mH,  $R_G = 25 \Omega$ ,  $I_D = -5 \text{ A}$ 

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.

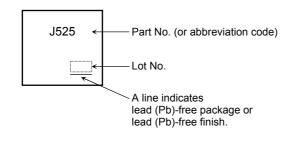
**Electrical Characteristics (Ta = 25°C)** 

Charac	teristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cu	rrent	I <sub>GSS</sub>	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0 V		_	±10	μA	
Drain cut-off cu	rrent	I <sub>DSS</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	-100	μA	
Drain−source br voltage	eakdown	V (BR) DSS	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0 V	-30	_	_	V	
Gate threshold v	voltage	V <sub>th</sub>	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -1 \text{ mA}$	-0.8	_	-2.0	V	
Drain-source ON resistance		R <sub>DS (ON)</sub>	$V_{GS}$ = -4 V, I <sub>D</sub> = -2.5 A	—	0.17	0.2	Ω	
			V <sub>GS</sub> = -10 V, I <sub>D</sub> = -2.5 A	_	0.1	0.12	12	
Forward transfer	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -2.5 A	2.0	4.5	_	S	
Input capacitance	e	C <sub>iss</sub>			850	_	pF	
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS}$ = -10 V, $V_{GS}$ = 0 V, f = 1 MHz	_	250	_		
Output capacitance		Coss			330	_		
Switching time	Rise time	tr	$V_{GS} = 10V$ $V_{GS} = 10V$ $V_{DD} = -15V$ $Duty \le 1\%, t_{W} = 10\mu s$	_	50	_		
	Turn-on time	t <sub>on</sub>		_	75	_	• ns	
	Fall time	t <sub>f</sub>			20	_		
	Turn-off time	t <sub>off</sub>			95	_		
Total gate charge (Gate-source plus gate-drain)		Qg	V <sub>DD</sub> ≈ −24 V, V <sub>GS</sub> = −10 V,	_	27	_		
Gate-source charge		Q <sub>gs</sub>	$I_{\rm D} = -5 \text{ A}$		19	_	nC	
Gate-drain ("miller") charge		Q <sub>gd</sub>			8	—		

## Source–Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	—	-	_	-5	А
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	—	-	-	-20	A
Forward voltage (diode)	V <sub>DSF</sub>	I <sub>DR</sub> = -5 A, V <sub>GS</sub> = 0 V	_	_	1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = -5 A, V <sub>GS</sub> = 0 V	_	60	—	ns
Reverse recovery charge	Q <sub>rr</sub>	dI <sub>DR</sub> / dt = 50 A / μs	_	56	_	nC

## Marking



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20070701-EN

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